



March 1998

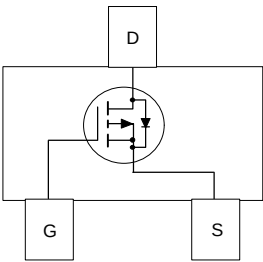
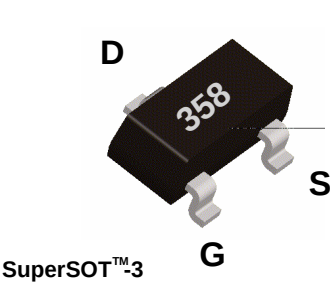
FDN358P
P-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

SuperSOT™-3 P-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications in notebook computers, portable phones, PCMCIA cards, and other battery powered circuits where fast switching, and low in-line power loss are needed in a very small outline surface mount package.

Features

- -1.5 A, -30 V, $R_{DS(ON)} = 0.125\ \Omega$ @ $V_{GS} = -10\text{ V}$
 $R_{DS(ON)} = 0.20\ \Omega$ @ $V_{GS} = -4.5\text{ V}$.
- High power version of industry SOT-23 package: identical pin out to SOT-23; 30% higher power handling capability.
- High density cell design for extremely low $R_{DS(ON)}$.
- Exceptional on-resistance and maximum DC current capability.



Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$ unless other wise noted

Symbol	Parameter	FDN358P	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain/Output Current - Continuous - Pulsed	-1.5	A
		-5	
P_D	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5	W
		0.46	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^{\circ}\text{C/W}$

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA	-30			V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	I _D = -250 μA, Referenced to 25 °C		-28		mV/ °C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -24 V, V _{GS} = 0 V			-1	μA
		T _J = 55°C			-10	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-1	-1.5	-2	V
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Temp. Coefficient	I _D = -250 μA, Referenced to 25 °C		3		mV/ °C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -1.5 A		0.11	0.125	Ω
		T _J =125°C		0.15	0.21	
		V _{GS} = -4.5 V, I _D = -1.2 A		0.175	0.2	
I _{D(on)}	On-State Drain Current	V _{GS} = -4.5 V, V _{DS} = -5 V	-5			A
g _{FS}	Forward Transconductance	V _{DS} = -10 V, I _D = -1.5 A		7		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V, f = 1.0 MHz		270		pF
C _{oss}	Output Capacitance			150		pF
C _{rss}	Reverse Transfer Capacitance			45		pF
SWITCHING CHARACTERISTICS (Note 2)						
t _{D(on)}	Turn - On Delay Time	V _{DD} = -15 V, I _D = -1 A, V _{GS} = -10 V, R _{GEN} = 6 Ω		8	16	ns
t _r	Turn - On Rise Time			7	14	ns
t _{D(off)}	Turn - Off Delay Time			17	27	ns
t _f	Turn - Off Fall Time			10	1.8	ns
Q _g	Total Gate Charge	V _{DS} = -5 V, I _D = -1.5 A, V _{GS} = -10 V		6.5	9.1	nC
Q _{gs}	Gate-Source Charge			1		nC
Q _{gd}	Gate-Drain Charge			1.1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				-0.42	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -0.42 A (Note 2)		-0.74	-1.2	V

Note:

1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.

Typical R_{θJA} using the board layouts shown below on FR-4 PCB in a still air environment :



a. 250°C/W when mounted on
0.02 in² pad of 2oz Cu.

a



b. 270°C/W when mounted on
a 0.001 in² pad of 2oz Cu.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

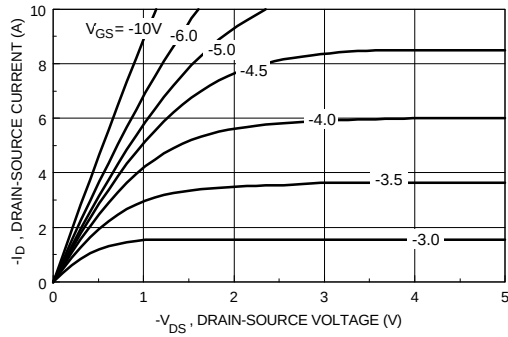


Figure 1. On-Region Characteristics.

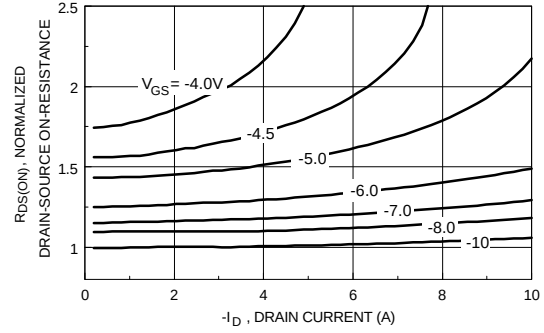


Figure 2. On-Resistance Variation with Drain Current and Gate

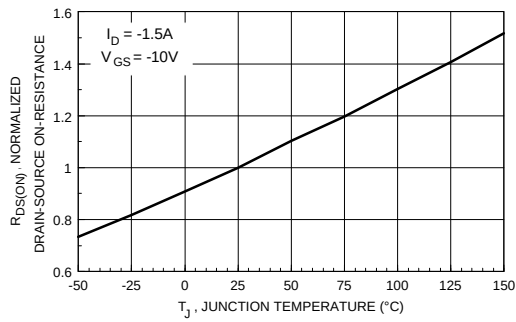


Figure 3. On-Resistance Variation with Temperature.

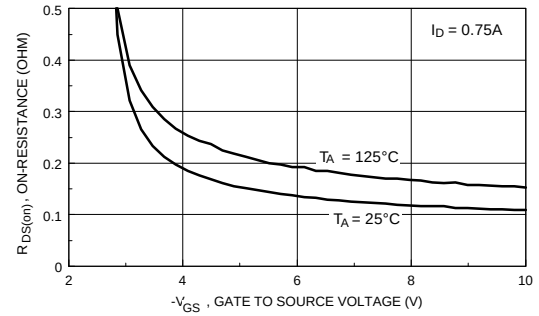


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

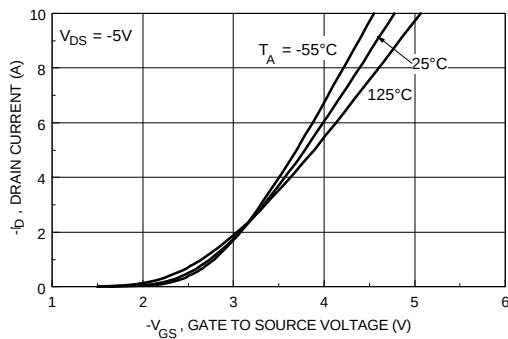


Figure 5. Transfer Characteristics.

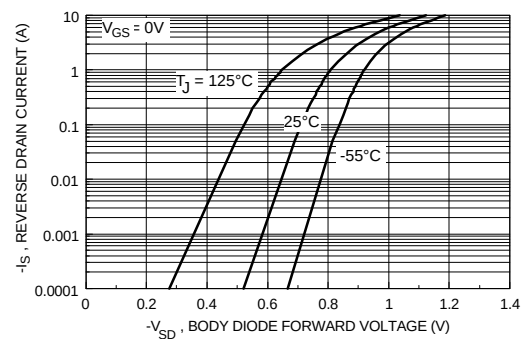


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics

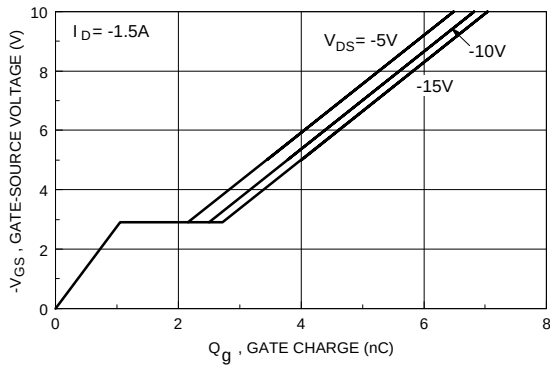


Figure 7. Gate Charge Characteristics.

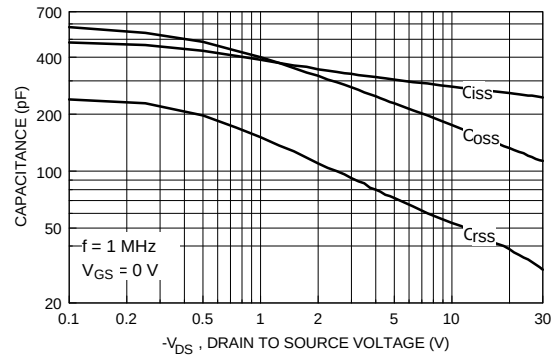


Figure 8. Capacitance Characteristics.

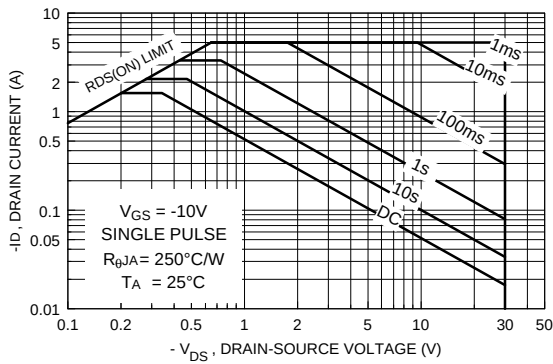


Figure 9. Maximum Safe Operating Area.

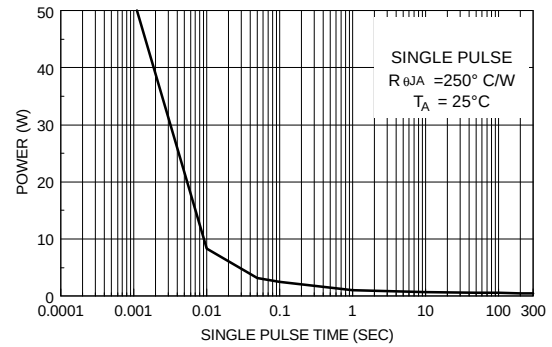


Figure 10. Single Pulse Maximum Power Dissipation.

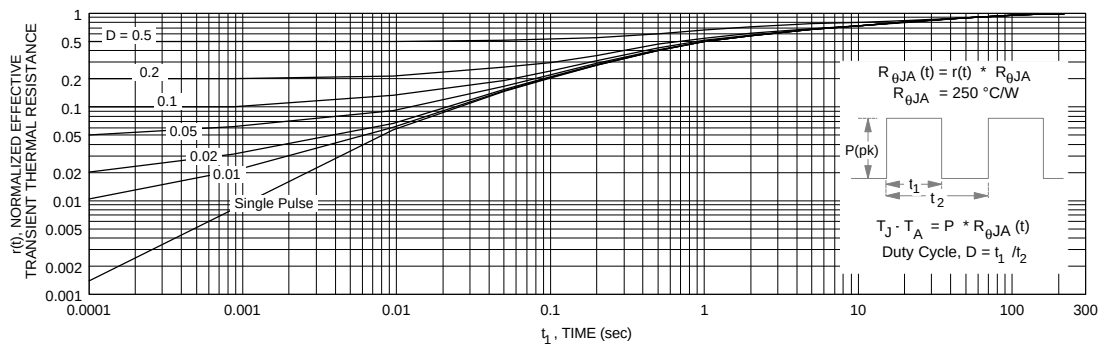


Figure 11. Transient Thermal Response Curve.